74HC2G32-Q100; 74HCT2G32-Q100

Dual 2-input OR gate

Rev. 2 — 6 January 2014

Product data sheet

1. General description

The 74HC2G32-Q100; 74HCT2G32-Q100 is a dual 2-input OR gate. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of $V_{\rm CC}$.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 2.0 V to 6.0 V
- Input levels:
 - For 74HC2G32-Q100: CMOS level
 - ◆ For 74HCT2G32-Q100: TTL level
- Complies with JEDEC standard no. 7A
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ♦ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)



3. Ordering information

Table 1. Ordering information

Type number	Package										
	Temperature range	Name	Description	Version							
74HC2G32DP-Q100	-40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8	SOT505-2							
74HCT2G32DP-Q100			leads; body width 3 mm; lead length 0.5 mm								
74HC2G32DC-Q100	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package;	SOT765-1							
74HCT2G32DC-Q100			8 leads; body width 2.3 mm								

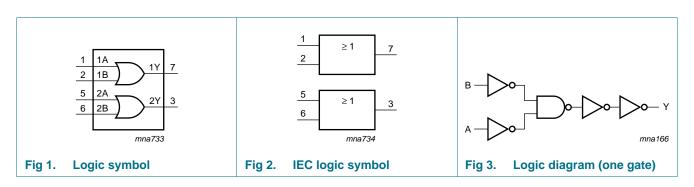
4. Marking

Table 2. Marking code

Type number	Marking code ^[1]
74HC2G32DP-Q100	H32
74HCT2G32DP-Q100	T32
74HC2G32DC-Q100	H32
74HCT2G32DC-Q100	T32

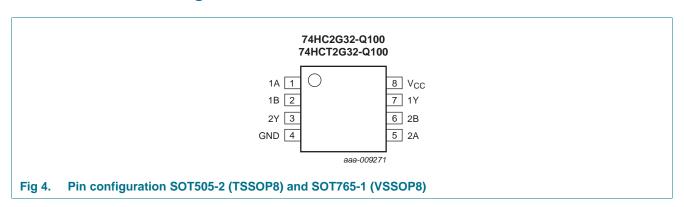
^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table[1]

Input		Output
nA	nB	nY
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

^[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	<u>[1]</u> _	25	mA
I _{CC}	supply current		<u>[1]</u> _	50	mA
I_{GND}	ground current		<u>[1]</u> –50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P_D	dynamic power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	300	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74H	C2G32-C	100	74H0	Unit		
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_{I}	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
	and fall rate	V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC2G	32-Q100									
** *	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	8.0	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	-	1.8	V

74HC_HCT2G32_Q100

All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2014. All rights reserved.

^[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

Table 7. Static characteristics ...continued Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C 1	to +125 °C	Ur
			Min	Тур	Max	Min	Max	Min	Max	
√он	HIGH-level	$V_I = V_{IH}$ or V_{IL}				•				
	output voltage	$I_{O} = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	٧
		$I_O = -20 \mu A$; $V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	٧
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	٧
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.18	4.32	-	4.13	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.68	5.81	-	5.63	-	5.2	-	٧
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
output voltage		$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	٧
		$I_O = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	٧
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	1.0	-	10	-	20	μ
Cı	input capacitance		-	1.5	-	-	-	-	-	pl
74HCT20	G32-Q100									
V _{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -20 \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_0 = -4.0 \text{ mA}$	4.18	4.32	-	4.13	-	3.7	-	٧
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	Ι _Ο = 20 μΑ	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 4.0 \text{ mA}$	-	0.15	0.26	-	0.33	-	0.4	V
l _l	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	1.0	-	10	-	20	μ
Δl _{CC}	additional supply current	per input; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $V_{I} = V_{CC} - 2.1 \text{ V}; I_{O} = 0 \text{ A}$	-	-	300	-	375	-	410	μ
Cı	input capacitance		-	1.5	-	-	-	-	-	pl

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 6.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HC2G	32-Q100		·								
t _{pd}	propagation	nA, nB to nY; see Figure 5	[1]								
	delay	$V_{CC} = 2.0 \text{ V}$		-	24	75	-	95	-	110	ns
		$V_{CC} = 4.5 \text{ V}$		-	9.0	15	-	19	-	22	ns
		$V_{CC} = 6.0 \text{ V}$		-	7.0	13	-	16	-	20	ns
t _t	transition	nY; see Figure 5	[2]								
	time	$V_{CC} = 2.0 \text{ V}$		-	18	75	-	95	-	125	ns
		$V_{CC} = 4.5 \text{ V}$		-	6	15	-	19	-	25	ns
		$V_{CC} = 6.0 \text{ V}$			5	13	-	16	-	20	ns
C_{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}$; $f_i = 1 \text{ MHz}$; $V_I = \text{GND to } V_{CC}$	[3]	-	10	-	-	-	-	-	pF
74HCT2	G32-Q100										
t _{pd}	propagation	nA, nB to nY; see Figure 5	[1]								
	delay	$V_{CC} = 4.5 \text{ V}$		-	13	24	-	30	-	36	ns
t _t	transition	nY; see Figure 5	[2]								
	time	$V_{CC} = 4.5 \text{ V}$		-	6	15	-	19	-	22	ns
C_{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}$; $f_i = 1 \text{ MHz}$; $V_I = \text{GND to } V_{CC} - 1.5 \text{ V}$	[3]	-	11	-	-	-	-	-	pF

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$

f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

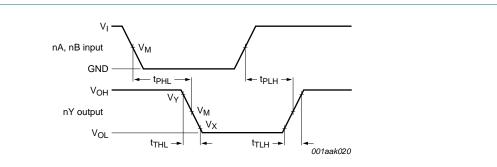
N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

^[2] t_t is the same as t_{TLH} and t_{THL} .

^[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

12. Waveforms



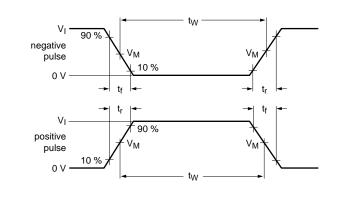
Measurement points are given in Table 9.

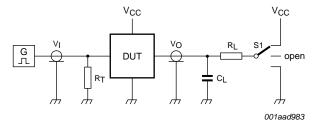
 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. Propagation delay data input (nA, nB) to data output (nY) and transition time output (nY)

Table 9. Measurement points

Туре	Input	Output	Output								
	V_{M}	V _M	V _X	V _Y							
74HC2G32-Q100	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}							
74HCT2G32-Q100	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}							





Test data is given in Table 10.

Definitions for test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

 R_1 = Load resistance.

S1 = Test selection switch.

Fig 6. Test circuit for measuring switching times

Table 10. Test data

Туре	Input		Load	Load				
	V _I	t _r , t _f	C _L	R _L	t _{PHL} , t _{PLH}			
74HC2G32-Q100	GND to V _{CC}	≤ 6 ns	50 pF	1 kΩ	open			
74HCT2G32-Q100	GND to 3 V	≤ 6 ns	50 pF	1 kΩ	open			

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

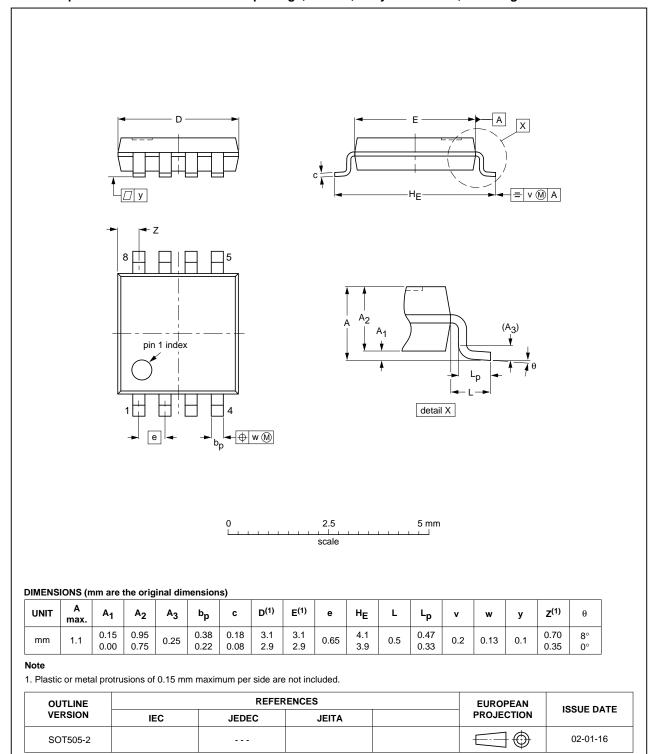


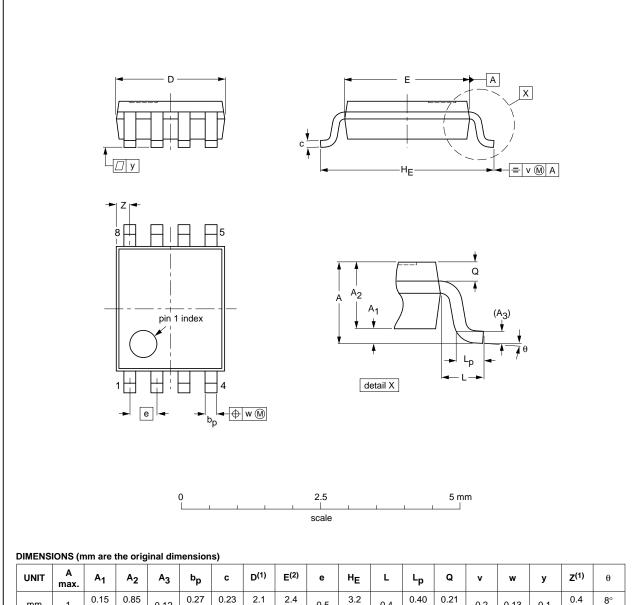
Fig 7. Package outline SOT505-2 (TSSOP8)

74HC_HCT2G32_Q100 All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2014. All rights reserved.

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	Α3	bp	C	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE	
	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT7	65-1		MO-187				02-06-07

Package outline SOT765-1 (VSSOP8)

74HC_HCT2G32_Q100

All information provided in this document is subject to legal disclaimers.

© NXP B.V. 2014. All rights reserved.

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G32_Q100 v.2	20140106	Product data sheet	-	74HC_HCT2G32_Q100 v.1
Modifications:	• For 74HC (errata).	T2G32-Q100 the condi	tions of C _{PD} are corre	ected to the family standard
74HC_HCT2G32_Q100 v.1	20131021	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

16.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

16.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Semiconductors product has been qualified for use in automotive applications. Unless otherwise agreed in writing, the product is not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for

inclusion and/or use of NXP Semiconductors products in such equipment or

applications and therefore such inclusion and/or use is at the customer's own

Suitability for use in automotive applications — This NXP

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

74HC_HCT2G32_Q100

74HC2G32-Q100; 74HCT2G32-Q100

NXP Semiconductors /4HC2G3

Dual 2-input OR gate

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Translations — A non-English (translated) version of a document is for reference only. The English version shall prevail in case of any discrepancy between the translated and English versions.

16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

17. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

74HC2G32-Q100; 74HCT2G32-Q100

NXP Semiconductors

Dual 2-input OR gate

18. Contents

1	General description
2	Features and benefits
3	Ordering information 2
4	Marking 2
5	Functional diagram 2
6	Pinning information 3
6.1	Pinning
6.2	Pin description
7	Functional description 3
8	Limiting values 4
9	Recommended operating conditions 4
10	Static characteristics 4
11	Dynamic characteristics 6
12	Waveforms
13	Package outline 9
14	Abbreviations
15	Revision history 11
16	Legal information
16.1	Data sheet status
16.2	Definitions
16.3	Disclaimers
16.4	Trademarks
17	Contact information
18	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.